



09/943078
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent of

U.S. Patent No. : 7,029,963 B2
Issued : April 18, 2006
Title : SEMICONDUCTOR DAMASCENE TRENCH AND METHODS
THEREOF
Docket No. : MIO 0083 PA/40509.162

Certificate of Corrections Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

CERTIFICATE OF MAILING
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on August 4, 2006.

James E. Beyer, Attorney

Reg. No. 39,564

Sir:

REQUEST FOR CERTIFICATE OF CORRECTION FOR PTO MISTAKE
UNDER 35 U.S.C. 254 and 37 C.F.R. 1.322

In the matter of U.S. Patent No. 7,029,963 B2, it is respectfully requested that a Certificate of Correction be issued to cover the following errors which occurred in the printing of the patent.

Col. 4, line 27 "the is isolation" should read --the isolation--;

Col. 7, line 38 "resistano" should read --resistance--; and

Claim 4 should be added as follows:

The method of fabricating a semiconductor device of claim 1, further
comprising:

shaping said spacer layer to form spacers against the vertical walls of said
damascene gate structure and said damascene interconnect structure.

Certificate
AUG 10 2006
of Correction

AUG 11 2006

REMARKS

It is respectfully requested that a Certificate of Correction be issued for the above-identified patent. All of the above errors occurred during the printing of the patent and, therefore, no fee is due. Two (2) copies of the required Certificate of Correction Form PTO/SB/44 are enclosed.

Respectfully submitted,
DINSMORE & SHOHL LLP

By


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JEB/tlo
Encl.

AUG 11 2006

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

Page 1 of 1

PATENT NO. : 7,029,963 B2
APPLICATION NO.: 09/943,078
ISSUE DATE : April 18, 2006
INVENTOR(S) : Todd R. Abbott

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 4, line 27 "the is isolation" should read --the isolation--;

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MAILING ADDRESS OF SENDER (Please do not use customer number below):

Dinsmore & Shohl, LLP
One Dayton Centre
One South Main Street, Suite 1300
Dayton, Ohio 45402

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: **Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

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Page 1 of 1

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